20 V, single P-channel Trench MOSFET 30 November 2012

Product data sheet

### 1. Product profile

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### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### **1.2 Features and benefits**

- 2.3 kV ESD protected
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

### 1.3 Applications

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- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

### 1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage	-		-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-5	А
Static charac	teristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -5 A; T <sub>j</sub> = 25 °C		-	39	48	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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### 2. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	D	drain		D	
2	D	drain			
3	G	gate		G ( The second s	
4	S	source			
5	D	drain	Transparent top view		
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa259	
7	D	drain			
8	S	source			

## 3. Ordering information

Table 3. Ordering information						
Type number	Package	'ackage				
	Name	Description	Version			
PMPB43XPE	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

### 4. Marking

Та	ble 4. Marking codes	
Ту	vpe number	Marking code
Ρ	MPB43XPE	1Y

## 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

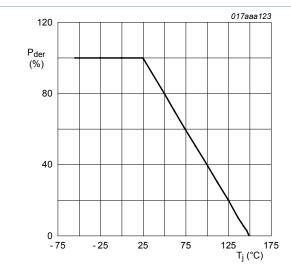
Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
gate-source voltage			-12	12	V
drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-5	А
	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-3.1	А
peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-12	А
total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
	T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.5	W
	drain-source voltage gate-source voltage drain current peak drain current	$\begin{array}{c} \mbox{drain-source voltage} \\ \mbox{drain source voltage} \\ \mbox{drain current} \\ \mbox{drain current} \\ \mbox{peak drain current} \\ \mbox{total power dissipation} \\ \end{array} \begin{array}{c} \mbox{T}_{j} = 25 \ ^{\circ}\text{C} \\ \mbox{V}_{GS} = -4.5 \ ^{\circ}\text{V}; \ \text{T}_{amb} = 25 \ ^{\circ}\text{C} \\ \mbox{V}_{GS} = -4.5 \ ^{\circ}\text{V}; \ \text{T}_{amb} = 100 \ ^{\circ}\text{C} \\ \mbox{T}_{amb} = 25 \ ^{\circ}\text{C}; \ \text{single pulse}; \ t_{p} \leq 10 \ ^{\mu}\text{s} \\ \mbox{T}_{amb} = 25 \ ^{\circ}\text{C} \end{array}$	$\begin{array}{c} \mbox{drain-source voltage} \\ \mbox{drain source voltage} \\ \mbox{drain current} \\ \mbox{drain current} \\ \mbox{peak drain current} \\ \mbox{total power dissipation} \\ \end{array} \begin{array}{c} \mbox{T}_{j} = 25 \ ^{\circ}\text{C} \\ \mbox{V}_{GS} = -4.5 \ ^{\circ}\text{V}; \ \mbox{T}_{amb} = 25 \ ^{\circ}\text{C} \\ \mbox{total power dissipation} \\ \mbox{T}_{amb} = 25 \ ^{\circ}\text{C} \\ \mbox{total power dissipation} \\ \end{array} \begin{array}{c} \mbox{T}_{amb} = 25 \ ^{\circ}\text{C} \\ \mbox{total power dissipation} \\ tota$	drain-source voltage $T_j = 25 \ ^{\circ}C$ -gate-source voltage $T_j = 25 \ ^{\circ}C$ -12drain current $V_{GS} = -4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C$ [1]- $V_{GS} = -4.5 \ V; \ T_{amb} = 100 \ ^{\circ}C$ [1]-peak drain current $T_{amb} = 25 \ ^{\circ}C; \ single pulse; \ t_p \le 10 \ \mu s$ -total power dissipation $T_{amb} = 25 \ ^{\circ}C$ [1]-	drain-source voltage $T_j = 25 \ ^{\circ}C$ 20gate-source voltage-1212drain current $V_{GS} = -4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C$ [1]5 $V_{GS} = -4.5 \ V; \ T_{amb} = 100 \ ^{\circ}C$ [1]3.1peak drain current $T_{amb} = 25 \ ^{\circ}C; \ single pulse; \ t_p \le 10 \ \mu s$ 12total power dissipation $T_{amb} = 25 \ ^{\circ}C$ [1]-1.7

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#### 20 V, single P-channel Trench MOSFET

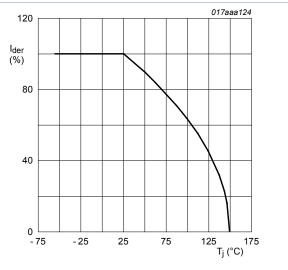
Symbol	Parameter	Conditions		Min	Мах	Unit
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain o	liode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.9	А
ESD maximum rating						
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	2300	V

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
 Measured between all pins.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

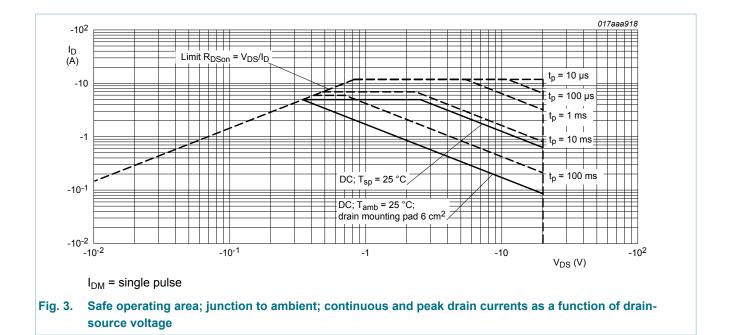




$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100 \%$$

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### 6. Thermal characteristics

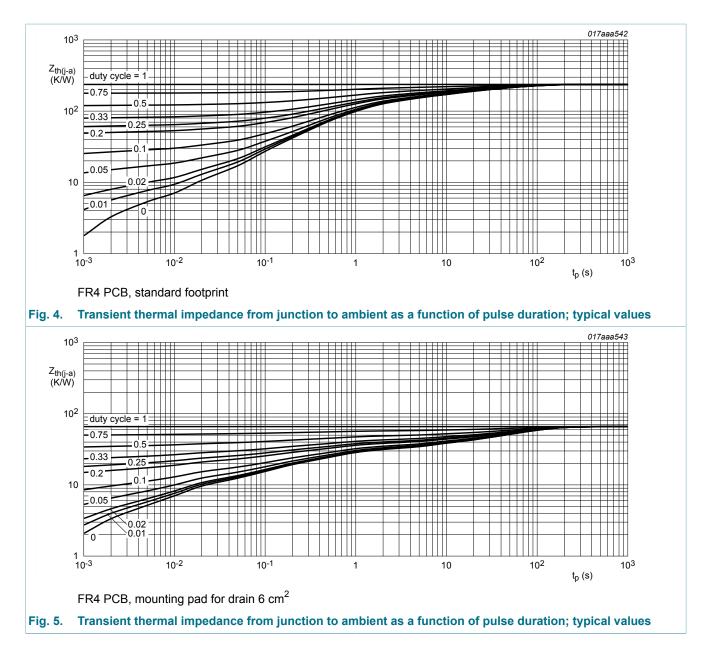
Table 6. T	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	33	36	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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### 7. Characteristics

Table 7. C	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics	·				
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.47	-0.68	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -5 A; T <sub>j</sub> = 25 °C	-	39	48	mΩ
	resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -5 A; T <sub>j</sub> = 150 °C	-	55	68	mΩ
		$V_{GS}$ = -2.5 V; I <sub>D</sub> = -4.5 A; T <sub>j</sub> = 25 °C	-	45	59	mΩ
		$V_{GS}$ = -1.8 V; I <sub>D</sub> = -3.7 A; T <sub>j</sub> = 25 °C	-	56	79	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -5 A; T <sub>j</sub> = 25 °C	-	20	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	5.6	-	Ω
Dynamic cl	haracteristics		I	I		
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -5 A; $V_{GS}$ = -4.5 V;	-	15.6	23.4	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.9	-	nC
Q <sub>GD</sub>	gate-drain charge		-	3.4	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -10 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	1550	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	142	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	116	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; I <sub>D</sub> = -5 A; V <sub>GS</sub> = -4.5 V;	-	9	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	38	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	57	-	ns
t <sub>f</sub>	fall time		_	25	-	ns

#### Source-drain diode

 $V_{SD}$ 

I<sub>S</sub> = -1.9 A; V<sub>GS</sub> = 0 V; T<sub>j</sub> = 25 °C

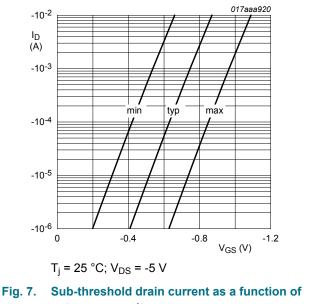
-1.2

V

-0.7

017aaa919 -12 -4.5 V -2.5 V -1.8 V I<sub>D</sub> (A) -1.6 V -8 -1.5 V -1.4 V -4 -1.3 V -1.2 V -V<sub>GS</sub> = -1.1 V 0 -1 -2 -3 \_\_\_\_\_\_ -4 0 T<sub>i</sub> = 25 °C Output characteristics: drain current as a Fig. 6. function of drain-source voltage; typical values

source-drain voltage



-

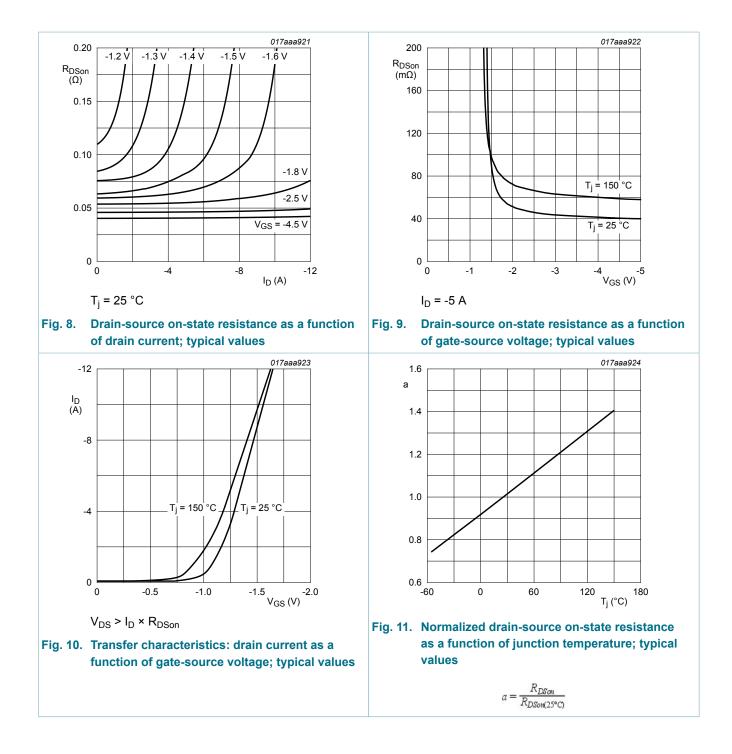
gate-source voltage

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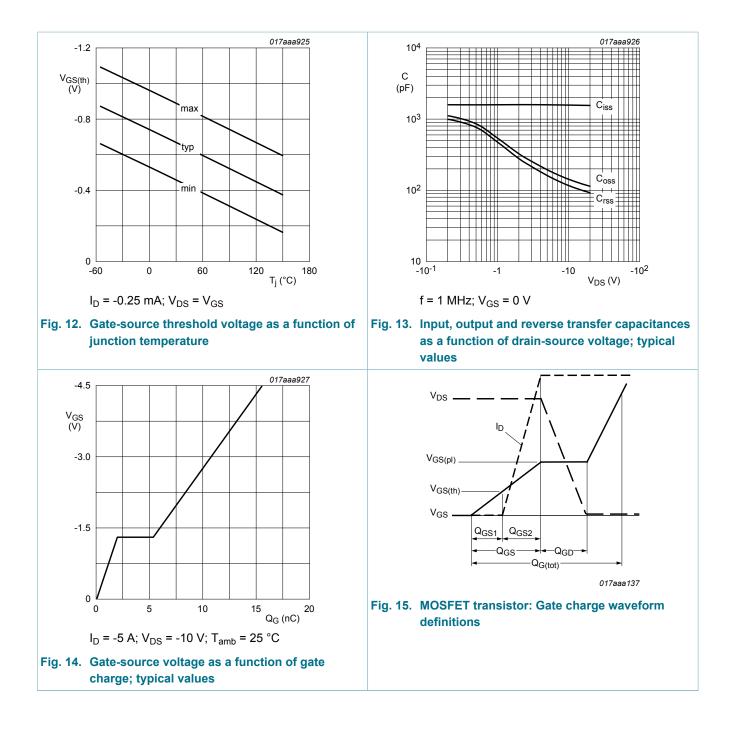
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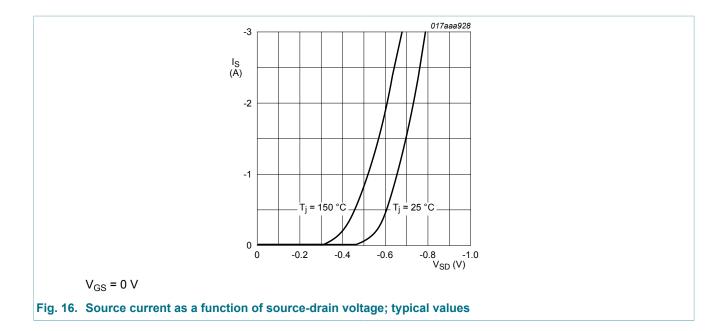
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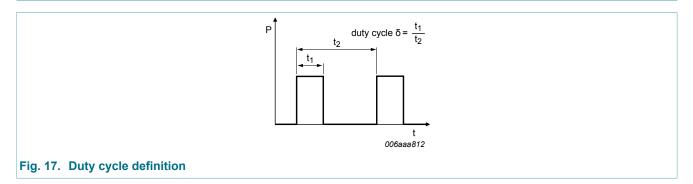


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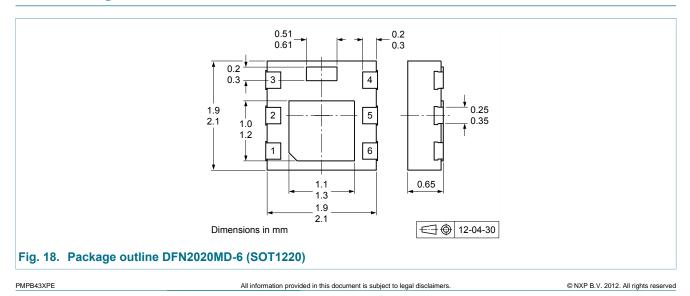
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### 8. Test information

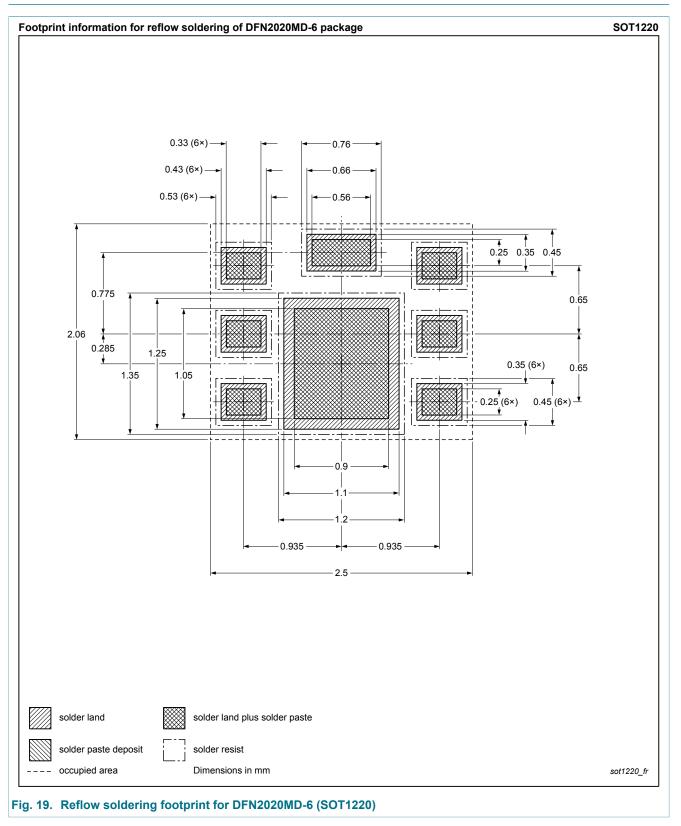


## 9. Package outline



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### **10. Soldering**



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## **11. Revision history**

Table 8.     Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMPB43XPE v.1	20121130	Product data sheet	-	-	

#### 20 V, single P-channel Trench MOSFET

### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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